



## **RFLM-200802MA-299**

### **Two Stage Passive Limiter Module - SMT**

#### **Features:**

- Surface Mount Limiter Module: 5mm x 8mm x 2.5mm
- Passive High Power PIN Limiter Design
- Frequency Range: 20 MHz to 8 GHz
- High Average Power Handling : 44dBm (CW)
- High Peak Power Handling: 51dBm
- Low Insertion Loss: 1.40 dB
- Low Flat Leakage Power : 20dBm
- Low Spike Energy Leakage: 0.2 ergs
- No external control lines or power supply required
- RoHS Compliant

#### **Description:**

The RFLM-200802MA-290 SMT Silicon PIN Diode Limiter Module offer both High Power CW and PeakPower protection in the 20 MHz to 8 GHz frequency range. It is based on a proven hybrid assembly technique utilized extensively in high reliability, mission critical applications. The RFLM200802MA-290 offers excellent thermal characteristics in a compact, low profile 8mm x 5mm x 2.5mm package. The RFLM-200802MA-299 is designed for optimal small signal insertion loss permitting extremely low receiver noise figure while simultaneously offering excellent large input signal Flat Leakage for effective receiver protection in the 20 MHz to 8 GHz frequency range.

The limiter RF circuit characteristics provide outstanding passive receiver protection (always on) which protects against High Average Power up to 44 dBm, High Peak Power up to 51 dBmpulsed (pulse width = 1 usec, duty cycle = 0.1%), maintains low flat leakage to less than 20dBm (typical),and reduces Spike Leakage to less than 0.2 ergs.

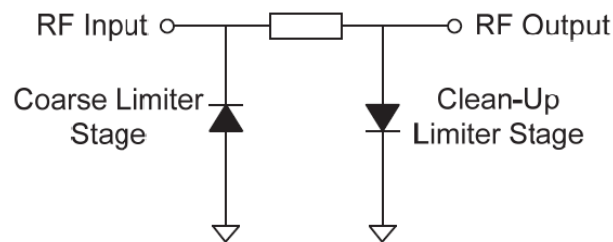
#### **ESD and Moisture Sensitivity Rating**

The RFLM200802MA-299 Limiter Module carries a Class 1C ESD rating (HBM) and an MSL 1 moisture rating.

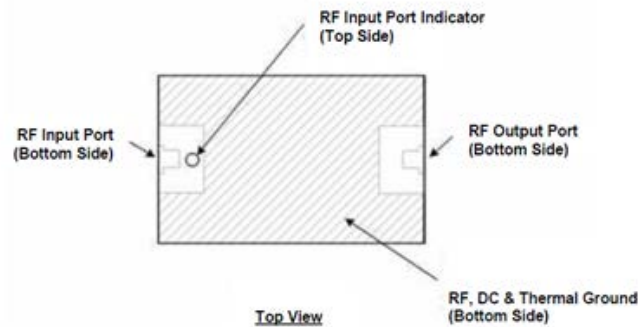
### Thermal Management Features

The RFLM-200802MA-299 based substrate has been design to offer superior long term reliability in the customer’s application by utilizing ultra-thin Au plating to combat Au embrittlement concerns. Also, a proprietary design methodology has minimized the thermal resistance from the PIN Diode junction to base plate ( $R_{THJ-A}$ ) to less than  $55^{\circ}\text{C}/\text{W}$ . The two stage limiter design employs a second stage limiter and quarter wavelength spacer detector circuit which permits ultra-fast turn on of the High Power PIN Diodes. This circuit topology couple with the thermal characteristic of the substrate design enables reliably handling High Input RF Power up to  $44\text{dBmCW}$  and RF Peak Power levels up to  $51\text{dBm}$  (1  $\mu\text{Sec}$  pulse width @ 0.1% duty cycle with base plate temperature at  $85^{\circ}\text{C}$ ).

### RFLM-200802MA-290 Limiter Module Schematic - No RF Coupling Capacitors



### Pin Out



## Absolute Maximum Ratings

@  $Z_0=50\Omega$ ,  $T_A=+25^\circ\text{C}$  as measured on the base ground surface of the device.

Parameter	Conditions	Absolute Maximum Value
Operating Temperature		$-65^\circ\text{C}$ to $125^\circ\text{C}$
Storage Temperature		$-65^\circ\text{C}$ to $150^\circ\text{C}$
Junction Temperature		$175^\circ\text{C}$
Assembly Temperature	T = 30 seconds	$260^\circ\text{C}$
RF Peak Incident Power	$T_{\text{CASE}}=85^\circ\text{C}$ , source and load VSWR < 1.2, RF Pulse width = 1 usec, duty cycle = 0.1%, derated linearly to 0 W at $T_{\text{CASE}}=150^\circ\text{C}$ (See note 1)	50dBm
RF CW Incident Power		42dBm
$\theta_{\text{JC}}$ Thermal Resistance		$55^\circ\text{C/W}$
Assembly Temperature		$260^\circ\text{C}$ for 30 seconds

Note 1:  $T_{\text{CASE}}$  is defined as the temperature of the bottom ground surface of the device.

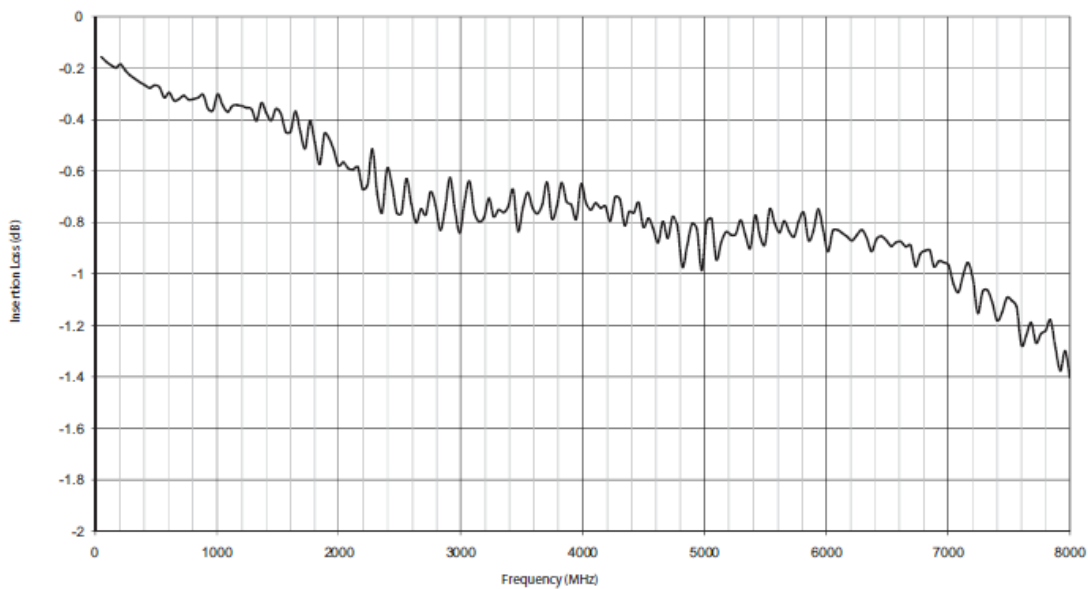
## RFLM200802MA-290 Electrical Specifications

@  $Z_0=50\Omega$ ,  $T_A=+25^\circ\text{C}$  as measured on the base ground surface of the device.

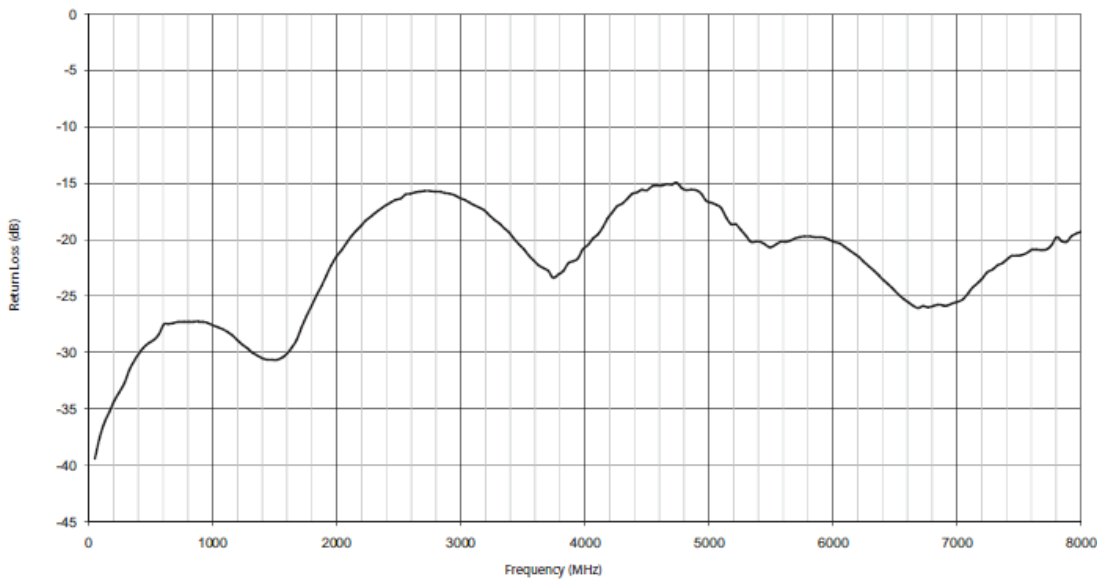
Parameters	Symbol	Test Conditions	Min Value	Typ Value	Max Value	Units
Frequency	F		0.020		8.0	GHz
Insertion Loss	IL	$20\text{ MHz} \leq F \leq 8\text{ GHz}$ , $P_{\text{in}}=0\text{ dBm}$		1.4	1.6	dB
Insertion Loss Rate of Change vs Operating Temperature	$\Delta\text{IL}$	$20\text{ MHz} \leq F \leq 8\text{ GHz}$ , $P_{\text{in}} \leq -10\text{ dBm}$		0.005		dB/ $^\circ\text{C}$
Return Loss	RL	$20\text{ MHz} \leq F \leq 8\text{ GHz}$ , $P_{\text{in}}=0\text{ dBm}$	13	15		dB
Input 1 dB Compression Point	$\text{IP}_{1\text{dB}}$	$20\text{ MHz} \leq F \leq 8\text{ GHz}$	6	8	10	dBm
2 <sup>nd</sup> Harmonic	$2F_0$	$P_{\text{in}}=0\text{ dBm}$ , $F_0=2.0\text{ GHz}$		-50	-40	dBc
Peak Incident Power	$P_{\text{inc(PK)}}$	RF Pulse = 1 usec, duty cycle = 0.1%, $t_{\text{rise}} \leq 2\text{ us}$ , $t_{\text{fall}} \leq 2\text{ usec}$		50	51	dBm
CW Incident Power	$P_{\text{inc(CW)}}$	$20\text{ MHz} \leq F \leq 8\text{ GHz}$		43	44	dBm
Flat Leakage	FL	$P_{\text{in}}=50\text{ dBm}$ , RF Pulse width = 1 us, duty cycle = 0.1%, $t_{\text{rise}} \leq 2\text{ us}$ , $t_{\text{fall}} \leq 2\text{ us}$		20	23	dBm
Spike Leakage	SL	$P_{\text{in}}=50\text{ dBm}$ , RF Pulse width = 1 us, duty cycle = 0.1%		0.2	0.3	erg
Recovery Time	$T_{\text{R}}$	50% falling edge of RF Pulse to 1 dB IL, $P_{\text{in}}=50\text{ dBm}$ peak, RF PW = 1 us, duty cycle = 0.1%, $t_{\text{rise}} \leq 2\text{ us}$ , $t_{\text{fall}} \leq 1\text{ usec}$		500	800	nsec

## RFLM-200802MA-299 Typical Performance

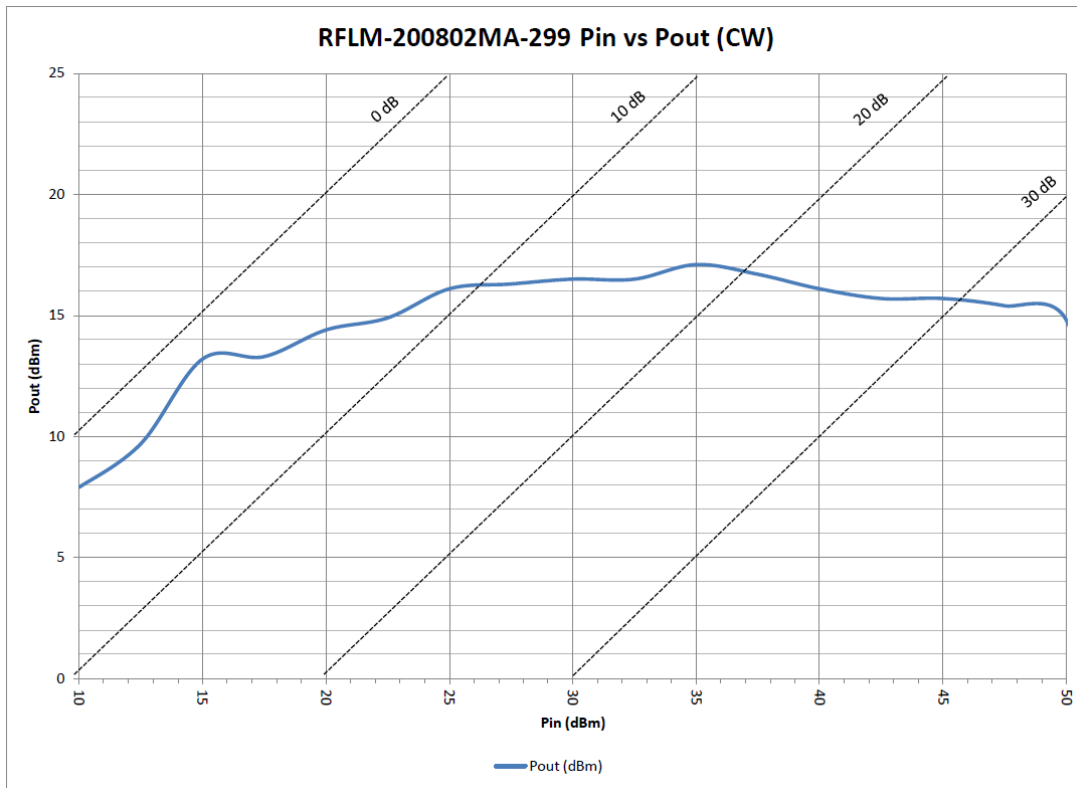
$Z_0 = 50\Omega$ ,  $T_{CASE} = 25^\circ\text{C}$ , PIN = 0 dBm as measured on the Ground Plane of the device.



Insertion Loss vs. Frequency



Return Loss vs Frequency



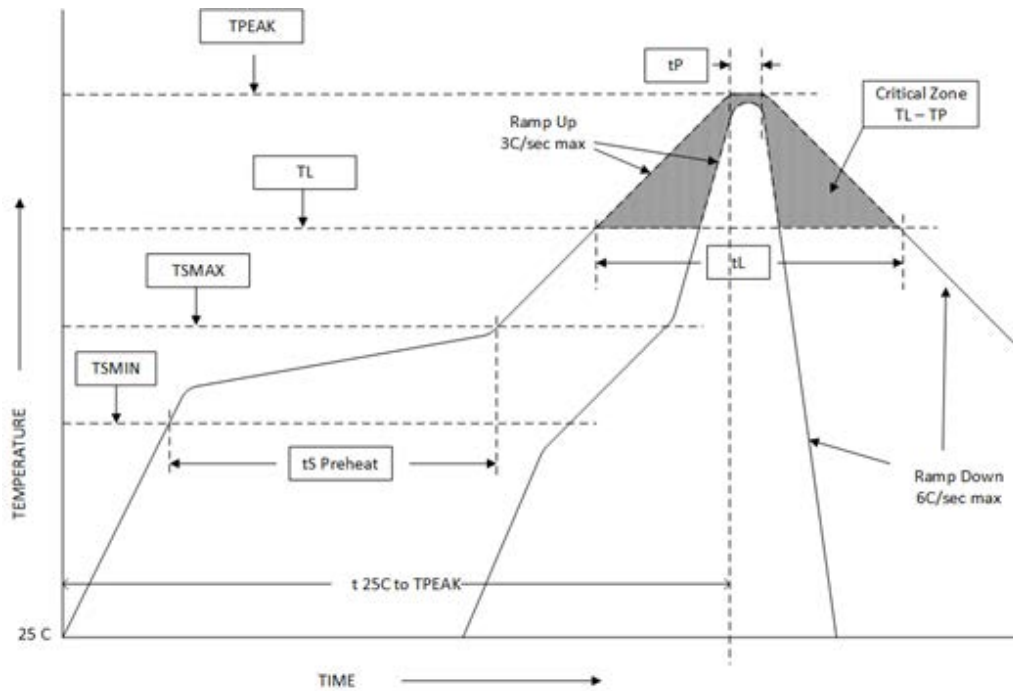
Pin vs Pout (CW)

### Assembly Instructions

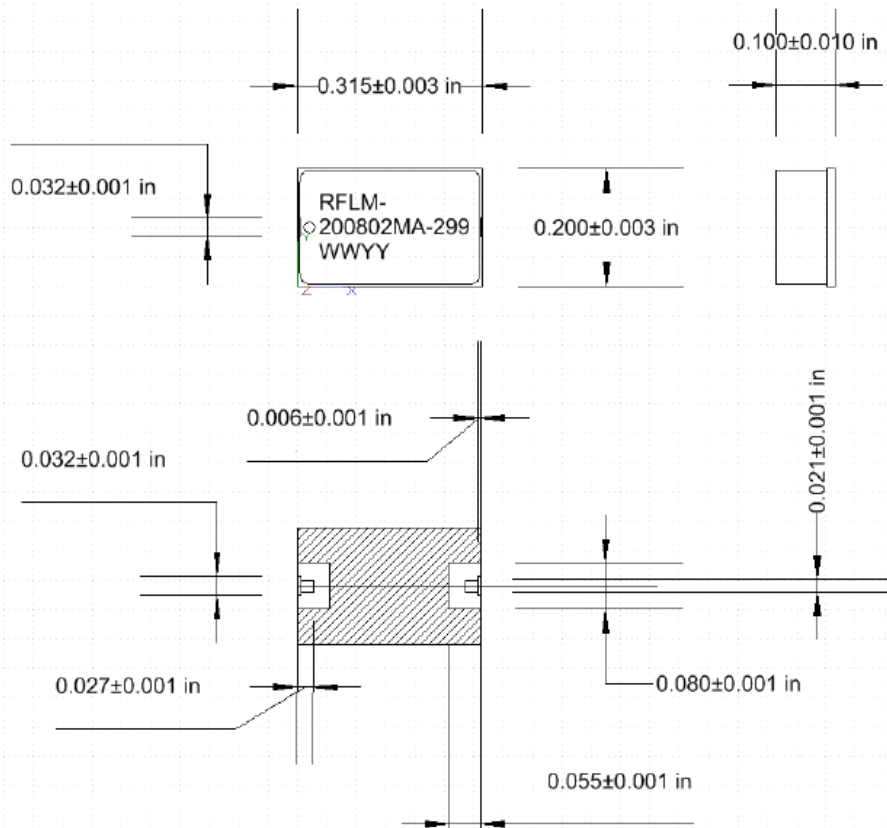
The RFLM-200802MA-299 may be attached to the printed circuit card using solder reflow procedures using either RoHS or Sn63/ Pb37 type solders per the Table and Temperature Profile Graph shown below:

Profile Parameter	Sn-Pb Assembly Technique	RoHS Assembly Technique
Average ramp-up rate ( $T_L$ to $T_P$ )	3°C/sec (max)	3°C/sec (max)
Preheat		
Temp Min ( $T_{smin}$ )	100°C	100°C
Temp Max ( $T_{smax}$ )	150°C	150°C
Time (min to max) ( $t_s$ )	60 – 120 sec	60 – 120 sec
$T_{smax}$ to $T_L$		
Ramp up Rate		3°C/sec (max)
Peak Temp ( $T_P$ )	225°C +0°C / -5°C	260°C +0°C / -5°C
Time within 5°C of Actual Peak Temp ( $T_P$ )	10 to 30 sec	20 to 40 sec
Time Maintained Above:		
Temp ( $T_L$ )	183°C	217°C
Time ( $t_L$ )	60 to 150 sec	60 to 150 sec
Ramp Down Rate	6°C/sec (max)	6°C/sec (max)
Time 25°C to $T_P$	6 minutes (max)	8 minutes (max)

### Solder Re-Flow Time-Temperature Profile



### RFLM-200802MA-299 Limiter Module Package Outline Drawing



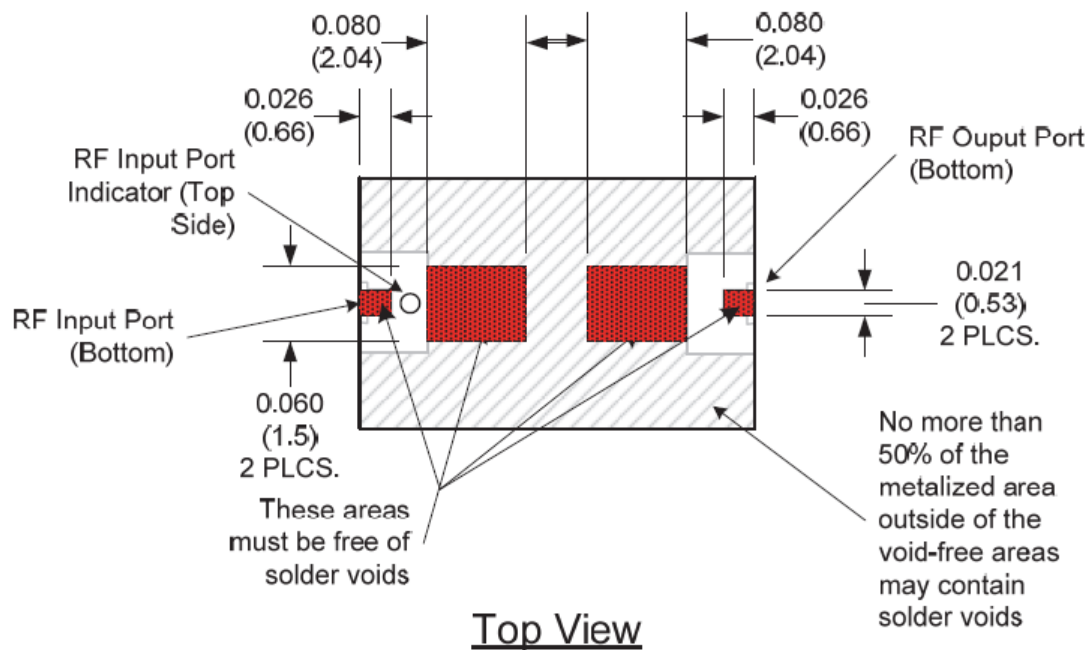
## Notes:

- 1) Metalized area on backside is the RF, DC and Thermal ground. In user's end application this surface temperature must be managed to meet the power handling requirements.
- 2) Back side metallization is thin Au termination plating to combat Au embrittlement (15 u in typ Au plated over Ti-Pd).

## Thermal Design Considerations:

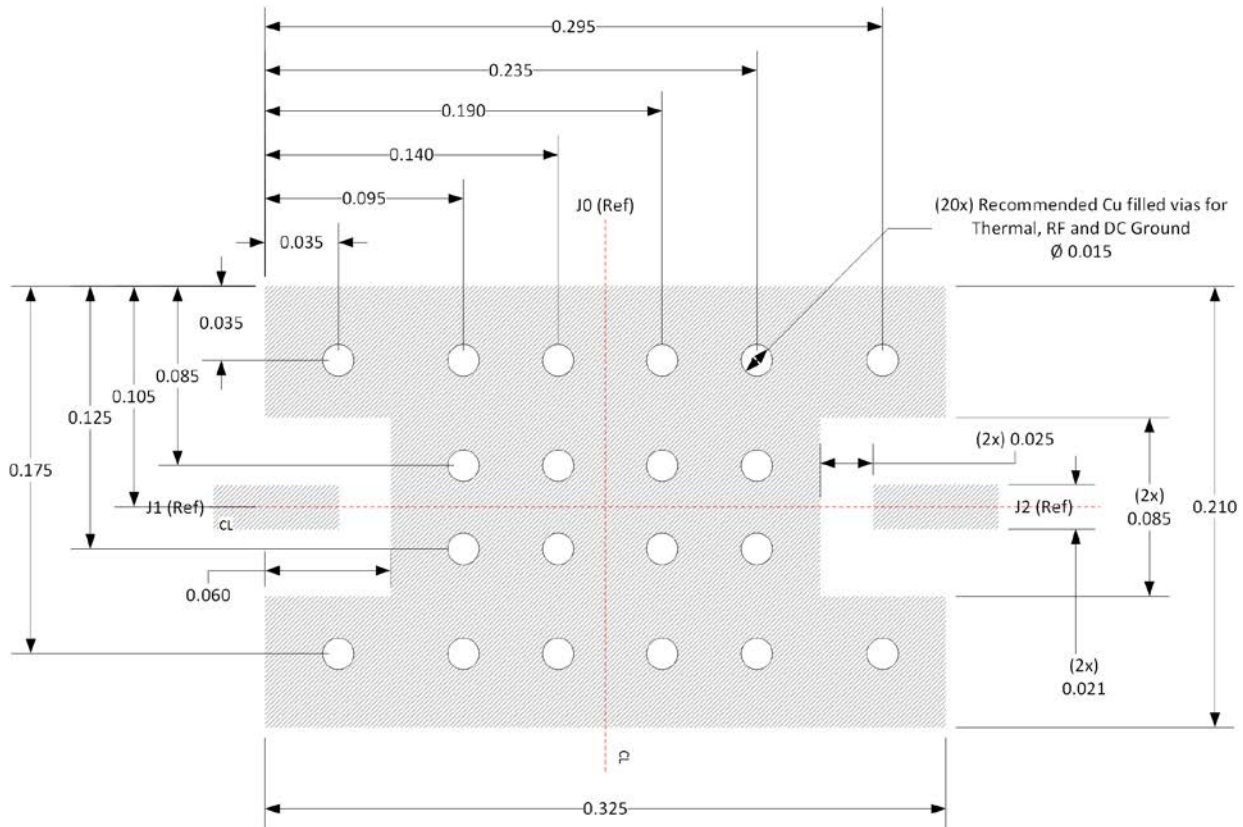
The design of the RFLM-200802MA-299 family of Limiter Modules permits the maximum efficiency in thermal management of the PIN Diodes while maintaining extremely high reliability. Optimum Limiter performance and reliability of the device can be achieved by the maintaining the base ground surface temperature of less than 85°C.

There must a minimal thermal and electrical resistance between the limiter and ground. Adequate thermal management is required to maintain a  $T_{jc}$  at less than +175°C and therefore will not adversely affect the semiconductor reliability. Special care must be taken to assure that minimal voiding occurs in the solder connection in the areas shade in red in the figure shown below.



Dimensions in inches (mm).

### Recommended RF Circuit Solder Footprint for the RFLM200802MA-290



Notes:

- 1) Recommended PCB material is rogers 4350, 10 mils thick.
- 2) Hatched area is RF, DC and Thermal Ground. Vias should be solid Cu filled and Au plated for optimal heat transfer from backside of Limiter Module through circuit vias to thermal ground.

### Part Number Ordering Detail:

The RFLM-200802MA-299 Limiter Module is available in either tube or Tape & Reel format.

Part Number	Description	Packaging
RFLM-200802MA-299	20 MHz to 8 GHz Band Limiter, No DC Blocking Caps	Tube
RFLM-200802MA-299TR	20 MHz to 8 GHz Band Limiter, No DC Blocking Caps	TR (250 pcs)